

N-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$V_{DS}(V)$ $R_{DS(on)}(\Omega)$				
200	1.2 at V _{GS} = 10 V	0.6			

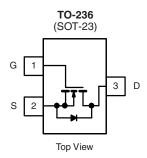
FEATURES

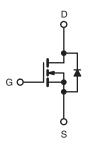
- DT-Trench Power MOSFET
- 100 % R_g Tested 100 % UIS Tested

COMPLIANT

APPLICATIONS

- · Load switch
- Power management for mobile computing





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	200	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I-	0.6		
Continuous Diain Current (1) = 150 C)	T _A = 70 °C	I _D	0.5	Α	
Pulsed Drain Current ^b		I _{DM}	2.5	1 ^	
Avalanche Current ^b	L = 0.1 mH	I _{AS}	2.5		
Single Avalanche Energy	L = U.T IIIII	E _{AS}	53	mJ	
Continuous Source Current (Diode Conduction) ^a		I _S	0.6	А	
Power Dissipation ^a	T _A = 25 °C	В	1.56	W	
rower Dissipation	T _A = 70 °C	P _D	1.19		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 5 s	- R _{thJA}	75	100	°C/W
Maximum sunction-to-Ambient	Steady State		125	170	
Maximum Junction-to-Foot	Steady State	R_{thJF}	40	55	

Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. Pulse width limited by maximum junction temperature.



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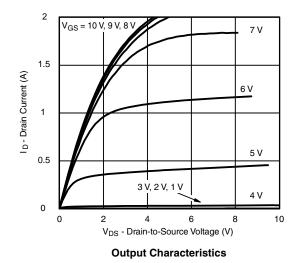
SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)							
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{DS} $V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$				V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.4	7 V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zoro Coto Voltago Drain Current	_	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 160 V, V_{GS} = 0 V, T_J = 70 °C	7!		75	- μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 15 \text{ V}, V_{GS} = 10 \text{ V}$	2.5			Α	
Drain-Source On-Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$		1.2	1.4	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ A}$		4		S	
Diode Forward Voltage	V_{SD}	$I_S = 1 A, V_{GS} = 0 V$		0.8	1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			3	5		
Gate-Source Charge	Q_{gs}	$V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$		0.37		nC	
Gate-Drain Charge	Q _{gd}			1.45			
Gate Resistance	R_g		0.5	1.3	2.4	Ω	
Switching							
Turn-On Delay Time	t _{d(on)}			7	13		
Rise Time	t _r	V_{DD} = 100 V, R_L = 33 Ω		10	16		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 0.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		9	15	ns	
Fall Time	t _f			11	15	1	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 0.5 A, dI/dt = 100 A/μs50100					

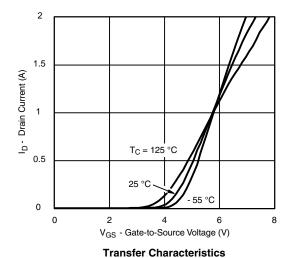
Notes:

- a. Pulse test: PW \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

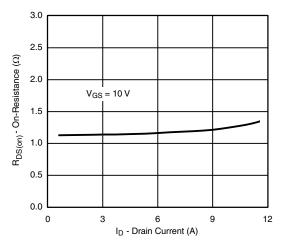
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



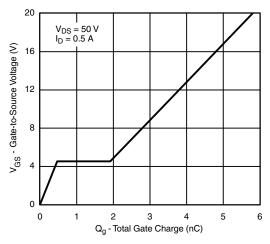




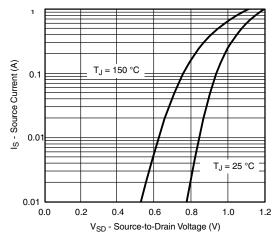
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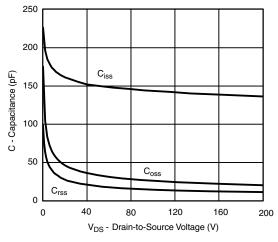
On-Resistance vs. Drain Current



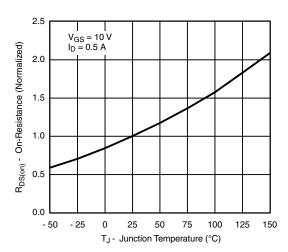
Gate Charge



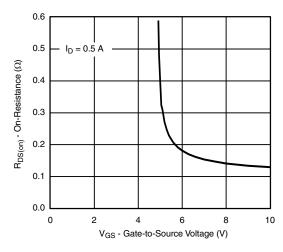
Source-Drain Diode Forward Voltage



Capacitance



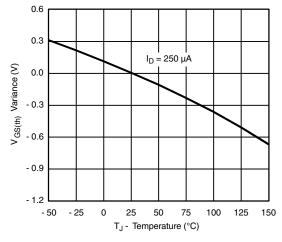
On-Resistance vs. Junction Temperature

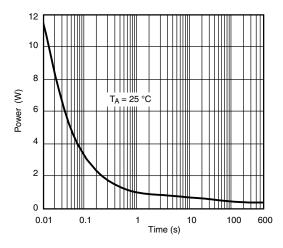


On-Resistance vs. Gate-to-Source Voltage



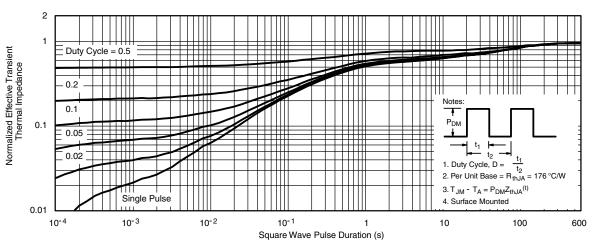
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Threshold Voltage

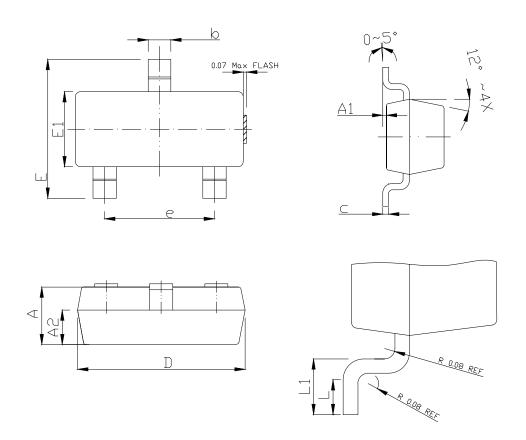




Normalized Thermal Transient Impedance, Junction-to-Ambient



SOT-23 PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MILLIMETER				
SIMDUL	MIN	NOM	MAX		
A	0.80	1.00	1.30		
A1	0.00	0.05	0.15		
b	0. 25	0.40	0.55		
С	0.11 BSC				
D	2 . 6 0	2.90	3. 20		
Е	2.10	2.40	2.70		
E1	1.10	1.30	1.48		
е	1.90 BSC				
L	0.17	_	_		
L1	0. 28	0.40	0.53		
A2	0.60 REF				





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